

# 2SK804

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## Silicon N-channel Power F-MOS FET

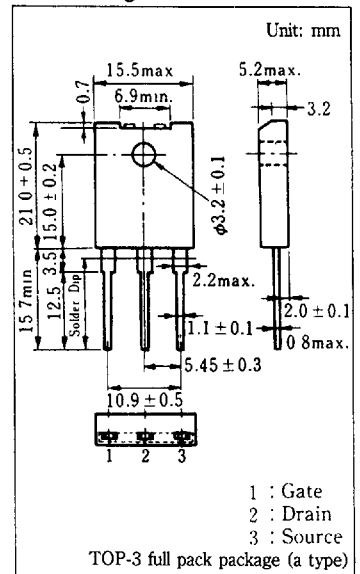
### ■ Features

- Low ON resistance  $R_{DS(on)}$  :  $R_{DS(on)} = 0.08\Omega$  (typ.)
- High switching rate :  $t_f = 150\text{ns}$  (typ.)
- No secondary breakdown
- High breakdown voltage

### ■ Application

- DC-DC converter
- No contact relay
- Solenoid drive
- Motor drive

### ■ Package Dimensions



### ■ Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	150	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Drain current	DC	$I_D$	20
	Peak-to-peak value	$I_{DP}$	40
Power dissipation	Tc=25°C	$P_D$	100
	Ta=25°C		3.0
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C

### ■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit	
Drain current	$I_{DS}$	$V_{DS} = 130\text{V}$ , $V_{GS} = 0$			0.1	mA	
Gate-source current	$I_{GS}$	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0$			$\pm 1$	$\mu\text{A}$	
Drain-source voltage	$V_{DS}$	$I_D = 1\text{mA}$ , $V_{GS} = 0$	160			V	
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{V}$ , $I_D = 1\text{mA}$	1		5	V	
Drain-source ON resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$ , $I_D = 10\text{A}$		0.08	0.12	$\Omega$	
Drain-source ON voltage	$V_{DS(on)}$	$V_{GS} = 10\text{V}$ , $I_{DS} = 20\text{A}$			2.5	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}$ , $I_D = 10\text{A}$	5.5	9.0		S	
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{V}$ , $V_{GS} = 0$ , $f = 1\text{MHz}$		1500		pF	
Output capacitance	$C_{oss}$				680		pF
Reverse transfer capacitance	$C_{rss}$				370		pF
Turn-on time	$t_{on}$		$V_{GS} = 10\text{V}$ , $I_D = 10\text{A}$		120		ns
Fall time	$t_f$	$V_{DD} = 100\text{V}$ , $R_L = 10\Omega$		150		ns	
Delay time	$t_d(\text{off})$				320		ns

$I_D - V_{DS}$   
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